



PMEG45A10EPD

45 V, 10 A low VF MEGA Schottky barrier rectifier

16 April 2014

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 10$ A
- Reverse voltage: $V_R \leq 45$ V
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

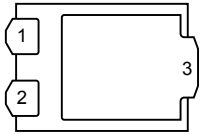
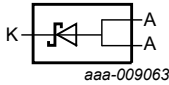
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 130$ °C; square wave	-	-	10	A
V_R	reverse voltage	$T_j = 25$ °C	-	-	45	V
V_F	forward voltage	$I_F = 10$ A; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_j = 25$ °C; pulsed	-	473	540	mV
I_R	reverse current	$V_R = 10$ V; $t_p \leq 3$ ms; $\delta = 0.3$; $T_j = 25$ °C; pulsed	-	13	30	μ A
		$V_R = 45$ V; $t_p \leq 3$ ms; $\delta = 0.3$; $T_j = 25$ °C; pulsed	-	150	500	μ A



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 CFP15 (SOT1289)	 aaa-009063
2	A	anode		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG45A10EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG45A10EPD	4510 AAAA

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	45	V
I_F	forward current	$T_{sp} = 125\text{ }^{\circ}\text{C}$; $\delta = 1$		-	14	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 130\text{ }^{\circ}\text{C}$; square wave		-	10	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; square wave		-	170	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	[1]	-	0.9	W
			[2]	-	1.2	W
			[3]	-	3	W
T_j	junction temperature			-	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-65	150	°C

- [1]

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3]

Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	165	K/W
			[1][3]	-	-	120	K/W
			[1][4]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	4	K/W

- [1]

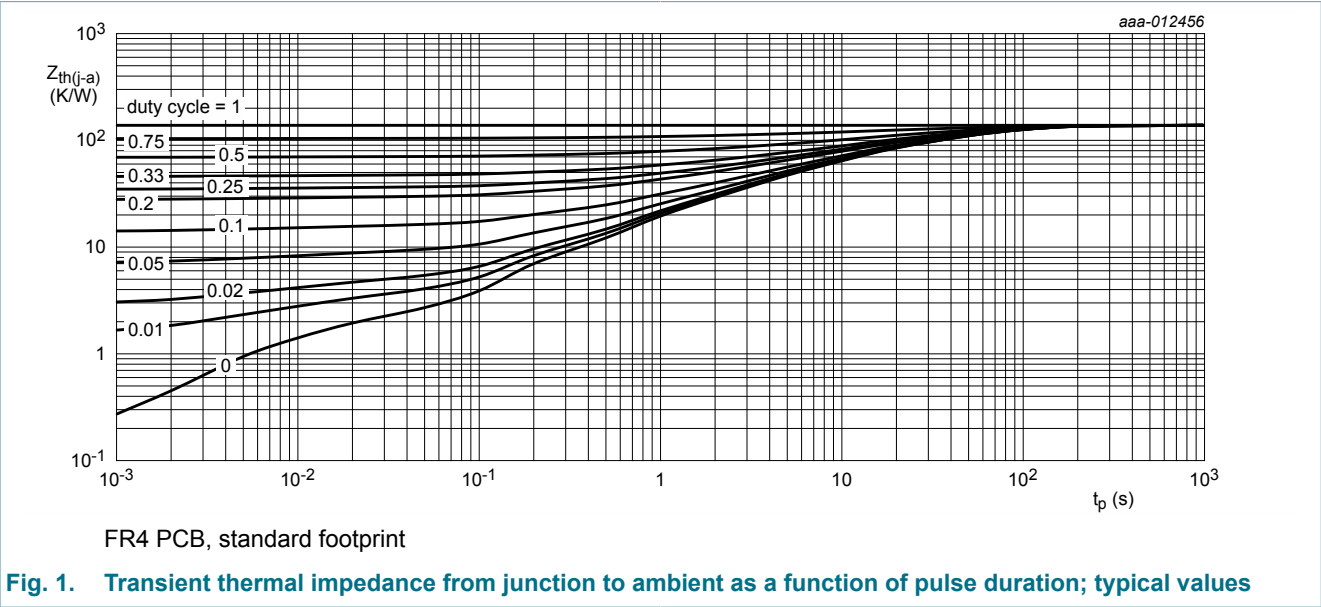
For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2]

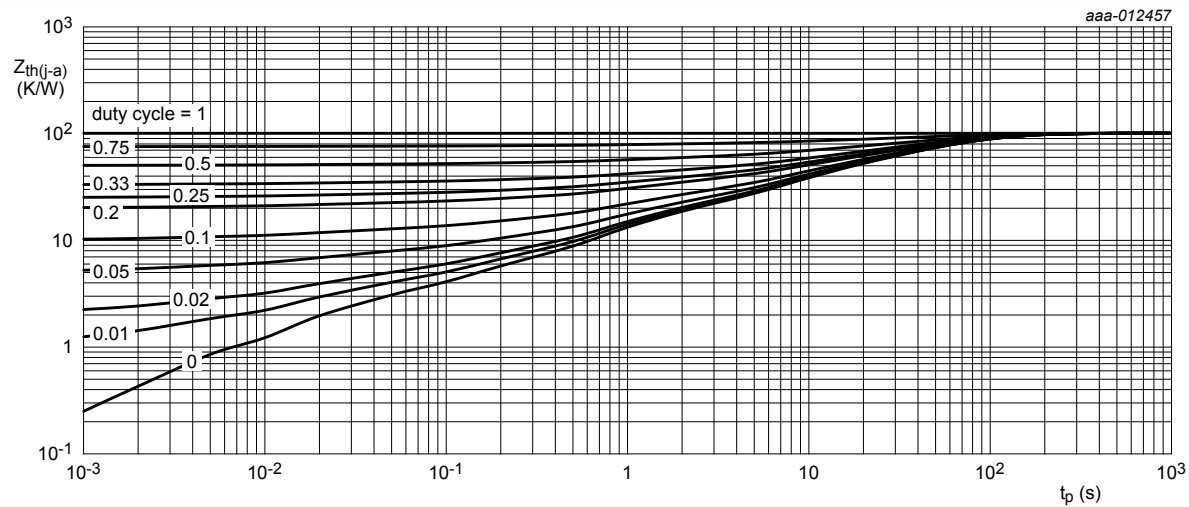
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4]

Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5]

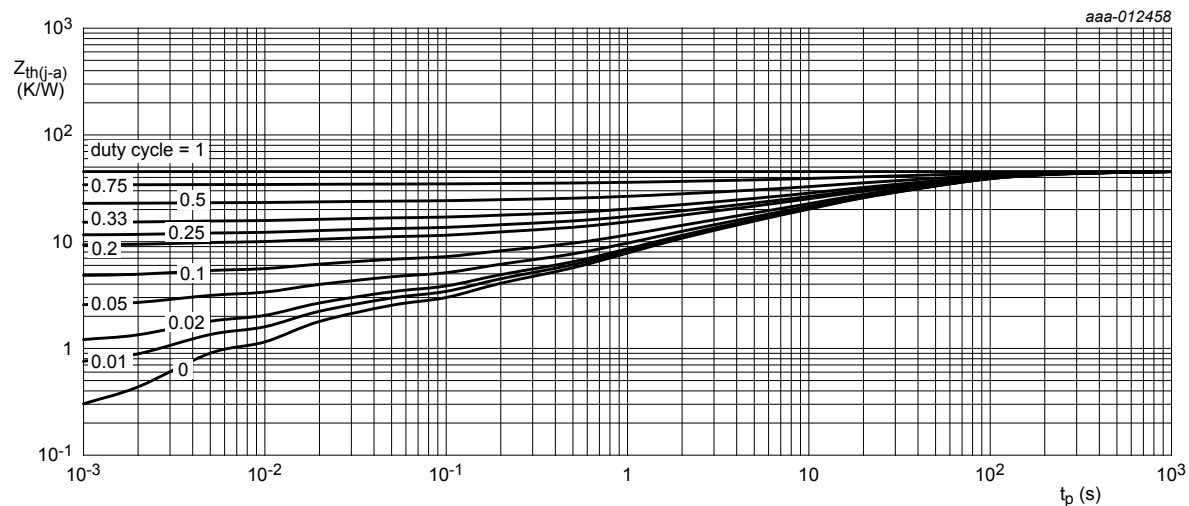
Soldering point of cathode tab.





FR4 PCB, mounting pad for cathode 1 cm²

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 1\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	330	380	mV
		$I_F = 2\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	357	-	mV
		$I_F = 3\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	377	-	mV
		$I_F = 5\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	409	470	mV
		$I_F = 10\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	473	540	mV
I_R	reverse current	$V_R = 5\text{ V}$; $t_p \leq 3\text{ ms}$; $\delta = 0.3$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	10	-	μA
		$V_R = 10\text{ V}$; $t_p \leq 3\text{ ms}$; $\delta = 0.3$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	13	30	μA
		$V_R = 30\text{ V}$; $t_p \leq 3\text{ ms}$; $\delta = 0.3$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	36	-	μA
		$V_R = 45\text{ V}$; $t_p \leq 3\text{ ms}$; $\delta = 0.3$; $T_J = 25\text{ }^\circ\text{C}$; pulsed	-	150	500	μA
		$V_R = 10\text{ V}$; $t_p \leq 3\text{ ms}$; $\delta = 0.3$; $T_J = 125\text{ }^\circ\text{C}$; pulsed	-	11	-	mA
C_d	diode capacitance	$V_R = 1\text{ V}$; $f = 1\text{ MHz}$; $T_J = 25\text{ }^\circ\text{C}$	-	715	-	pF
		$V_R = 10\text{ V}$; $f = 1\text{ MHz}$; $T_J = 25\text{ }^\circ\text{C}$	-	240	-	pF
t_{rr}	reverse recovery time ; step recovery	$I_F = 0.5\text{ A}$; $I_R = 0.5\text{ A}$; $I_{R(\text{meas})} = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$	-	21	-	ns
t_{rr}	reverse recovery time ; ramp recovery	$dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_J = 25\text{ }^\circ\text{C}$; $I_F = 6\text{ A}$; $V_R = 26\text{ V}$	-	13	-	ns
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 5\text{ mA}$; $T_J = 25\text{ }^\circ\text{C}$; $t_p \leq 1.2\text{ ms}$; $\delta = 0.12$; pulsed	45	-	-	V
V_{FRM}	peak forward recovery voltage	$I_F = 0.5\text{ A}$; $dI_F/dt = 20\text{ A}/\mu\text{s}$; $T_J = 25\text{ }^\circ\text{C}$	-	317	-	mV

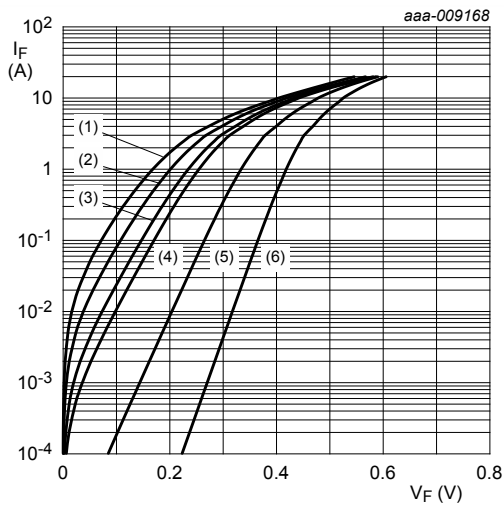


Fig. 4. Forward current as a function of forward voltage; typical values (pulsed condition)

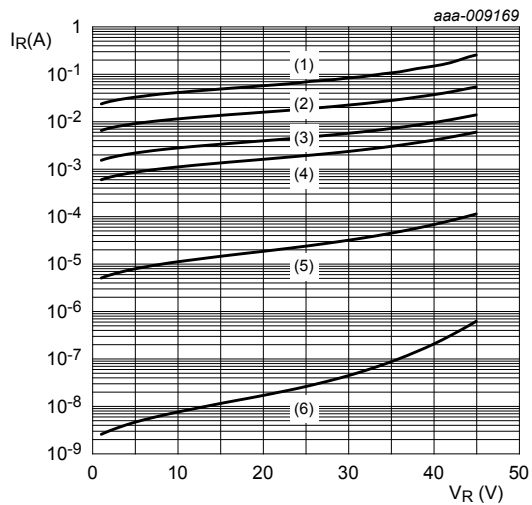
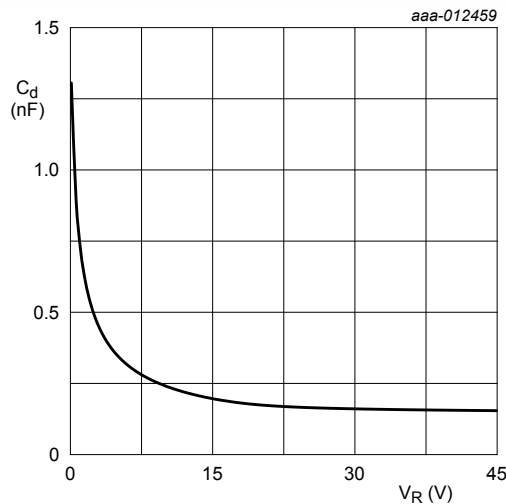


Fig. 5. Reverse current as a function of reverse voltage; typical values (pulsed condition)



$f = 1\text{ MHz}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values

11. Test information

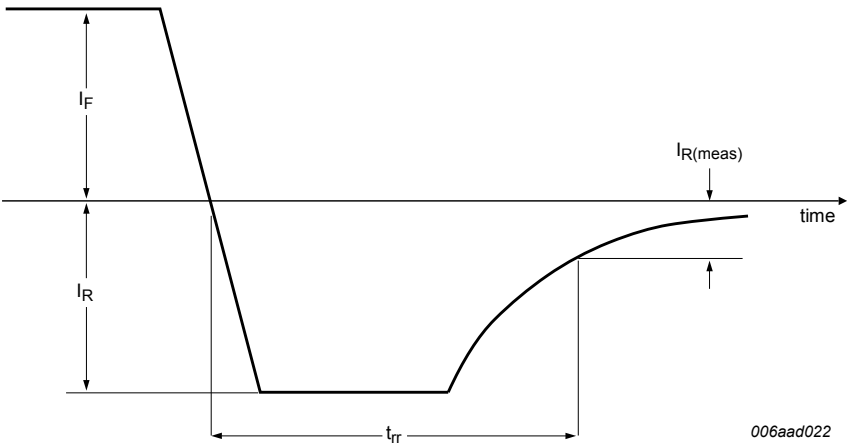


Fig. 7. Reverse recovery definition; step recovery

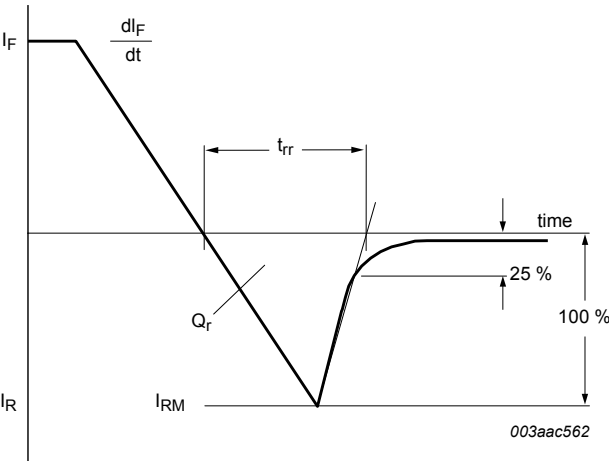


Fig. 8. Reverse recovery definition; ramp recovery

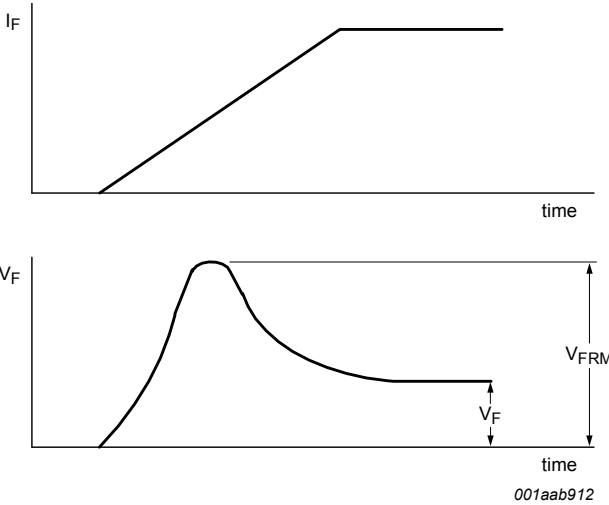


Fig. 9. Forward recovery definition

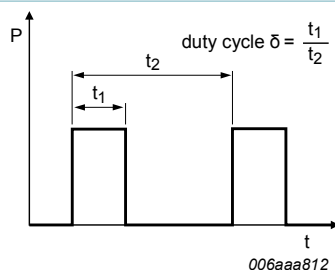


Fig. 10. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:
 $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

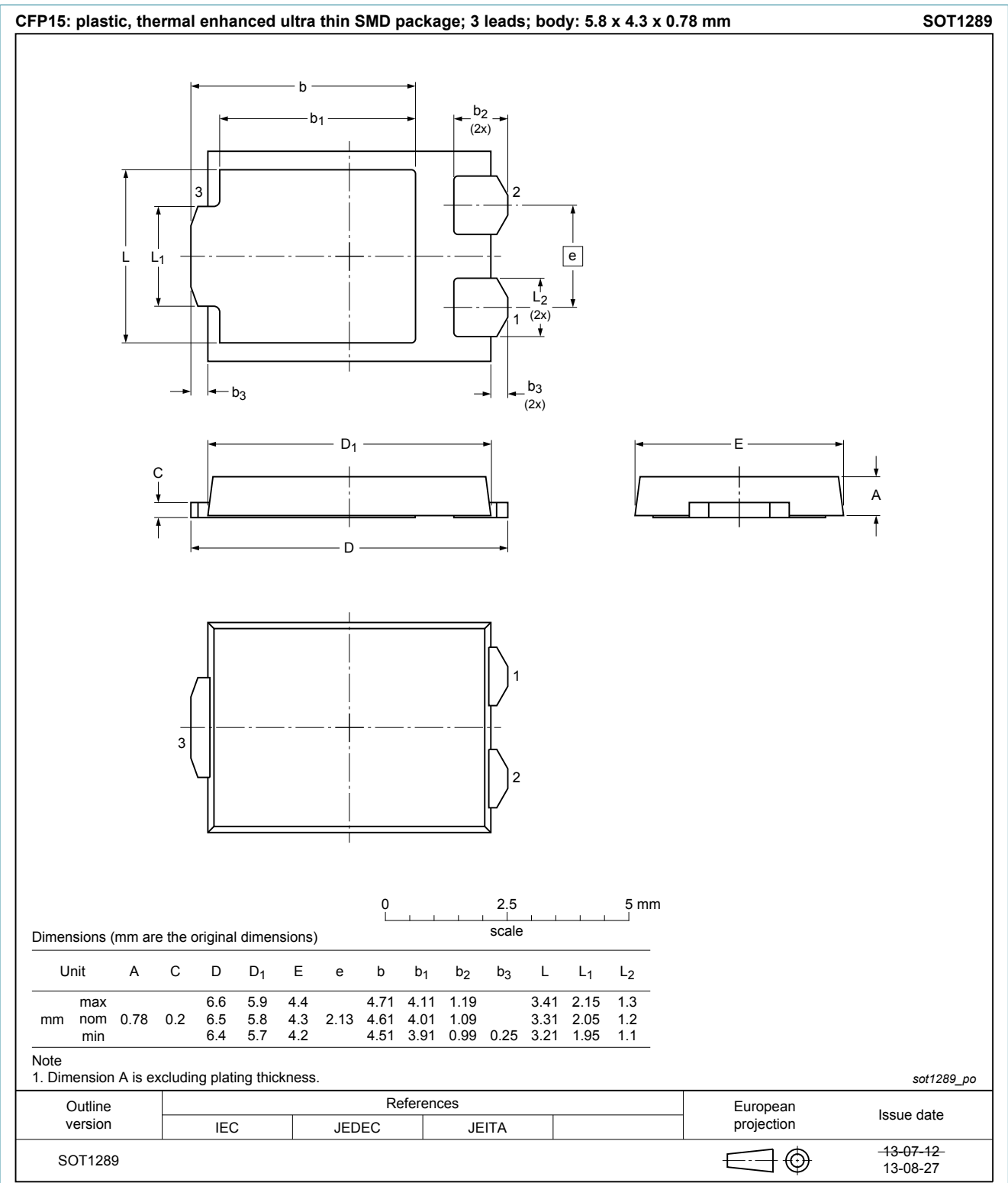


Fig. 11. Package outline CFP15 (SOT1289)

13. Soldering

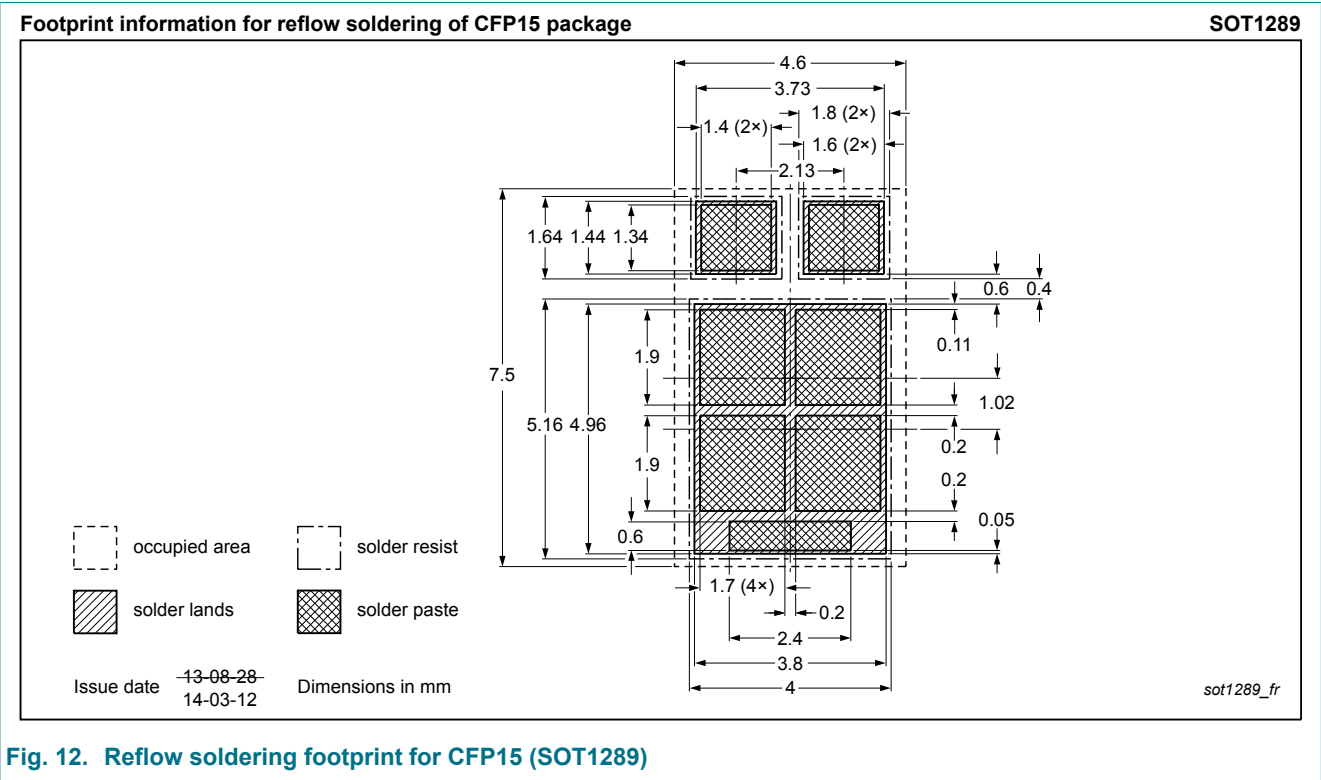


Fig. 12. Reflow soldering footprint for CFP15 (SOT1289)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG45A10EPD v.2	20140416	Product data sheet	-	PMEG45A10EPD v.1
Modifications:	<ul style="list-style-type: none">Product status changed			
PMEG45A10EPD v.1	20140217	Objective data sheet	-	-

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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